

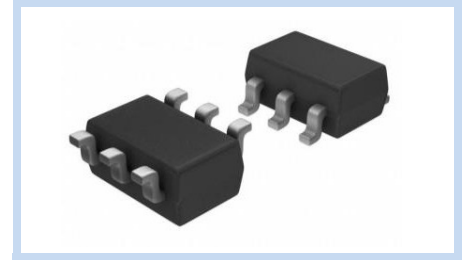
**2N Channel MOSFET**  
**60V 250mA 350mW ESD AEC-Q101**

MFT62NA25S363EA

**MERITEK**

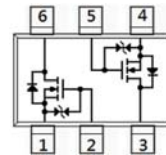
**FEATURE**

- $R_{DS(ON)} < 3\Omega$ ,  $V_{GS} = 10V$ ,  $I_D = 500mA$
- $R_{DS(ON)} < 4\Omega$ ,  $V_{GS} = 4.5V$ ,  $I_D = 200mA$
- Advanced Trench Process Technology
- ESD Protected 2KV HBM
- AEC-Q101 Qualified



**MECHANICAL DATA**

- Case: SOT-363 Package
- Terminals: Solderable per MIL-STD-750, Method 2026



**MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit	
Drain-Source Voltage	$V_{DS}$	60	V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V	
Drain Current – Continuous	$I_D$	250	mA	
Drain Current – Pulsed	$I_{DM}$	1000	mA	
Power Dissipation	$P_D$	$T_A = 25^\circ C$	350	mW
		Derate above $25^\circ C$	4	mW/ $^\circ C$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	357	$^\circ C/W$	
Operating Junction and Storage Temperature	$T_J, T_{STG}$	-55 to +150	$^\circ C$	

**DIMENSIONS**

Item	Min (mm)	Max (mm)
A1	0.00	0.10
A2	0.80	1.00
A3	-	1.10
b	0.15	0.30
C	0.08	0.25
D	1.90	2.20
e	0.55	0.75
e1	1.20	1.40
E	2.00	2.20
E1	1.15	1.35
L	0.15	0.45
Y		1.18
Y1		0.66
Y2		2.50
X		0.45
X1		0.65

